

IN THE CLAIMS:

Please amend the claims as follows:

Claims 1-2 (**Canceled**)

3. (**Currently Amended**) A method for fabricating a semiconductor laser device which emits a plurality of laser beams of different wavelengths, comprising:

 a first process for fabricating a first intermediate body on a semiconductor substrate, including a step of forming a first multi-layer stack having a semiconductor for forming a first lasing portion;

 a second process for fabricating a second intermediate body on a support substrate, including a step of forming a layer containing at least a light absorption layer of InGaN, a step of forming a second multi-layer stack of a semiconductor for forming a second lasing portion on said light absorption layer, and a step of forming a groove in said second multi-layer stack;

 a third process for fabricating a bonded body by securely adhering a face of said first intermediate body on a side of said first multi-layer stack to a face of said second intermediate body on a side of said second multi-layer stack via an electrically conductive adherent layer; and

 a fourth process for decomposing said light absorption layer by irradiating said light absorption layer with light through said support substrate of said bonded body to strip off at least said support substrate along said decomposed light absorption layer.

4. **(Original)** The method for fabricating a semiconductor laser device according to claim 3, wherein in said second process, said groove is formed to be deeper than a depth from a surface of said second multi-layer stack to said light absorption layer.

5. **(Previously Presented)** The method for fabricating a semiconductor laser device according to claim 3, wherein said light passes through said support substrate and is absorbed by said light absorption layer.

6. **(Currently Amended)** The method for fabricating a semiconductor laser device according to claim ~~[[1]]~~ 3, wherein at least one of said first process and said second process includes a process for forming said adherent layer on at least one of the face of said first intermediate body on the side of said first multi-layer stack and the face of said second intermediate body on the side of said second multi-layer stack.

7. **(Currently Amended)** The method for fabricating a semiconductor laser device according to claim ~~[[1]]~~ 3, wherein~~[[:]]~~

said first multi-layer stack has a III-V compound semiconductor containing any one of arsenic (As), phosphorus (P), and antimony (Sb) as a group V element or a II-VI compound semiconductor; and

said second multi-layer stack has a nitride-based III-V compound semiconductor with the group V element being nitrogen (N).

8. **(Currently Amended)** The method for fabricating a semiconductor laser device according to claim ~~[[1]]~~ 3, wherein said adherent layer is of a metal.

9. **(New)** The method for fabricating a semiconductor laser device according to claim 3, wherein an impurity is doped into said light absorption layer to serve as non-radiative recombination center.